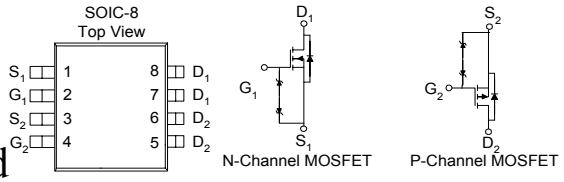
P & N-Channel 32-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	82 @ V_{GS} = 4.5V	4.2
	50 @ V_{GS} = 10V	5.3
-30	80 @ V_{GS} = -4.5V	-4.2
	52 @ V_{GS} = -10V	-5.2

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

ESD Protected
2000V



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		**Symbol**	**N-Channel**	**P-Channel**	**Units**
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	
Continuous Drain Current[a]	T_A=25°C	I_D	5.3	-5.2	A
	T_A=70°C		4.2	-4.1	
Pulsed Drain Current[b]		I_{DM}	20	-20	
Continuous Source Current (Diode Conduction)[a]		I_S	1.3	-1.3	A
Power Dissipation[a]	T_A=25°C	P_D	2.1	2.1	W
	T_A=70°C		1.3	1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W
	Steady-State		110	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	**Symbol**	**Test Conditions**	**Limits**				**Unit**
			Ch	**Min**	**Typ**	**Max**	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250 uA	N	1.2			V
		V_{GS} = V_{DS}, I_D = -250 uA	P	-1.2		-2.5	
Gate-Body Leakage	I_{GSS}	V_{GS} = -20 V, V_{DS} = 0 V	P			±100	nA
		V_{GS} = 20 V, V_{DS} = 0 V	N			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24 V, V_{GS} = 0 V	P			-1	uA
		V_{DS} = 24 V, V_{GS} = 0 V	N			1	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	N	20			A
		V_{DS} = -5 V, V_{GS} = -10 V	P	-20			
Drain-Source On-Resistance[A]	$r_{DS(on)}$	VGS = 10 V, I_D = 5.3 A	N			50	mΩ
		VGS = 4.5 V, I_D = 4.2 A				82	
		VGS = -10 V, I_D = -5.2 A	P			52	
		VGS = -4.5 V, I_D = -42 A				80	
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1.3 A	N		0.75		V
		V_{GS} = 0 V, I_S = -1.3 A	P		-0.88		
Dynamic							
Total Gate Charge	Q_g	N-Channel V_{DS}=15V, V_{GS}=10V, I_D=5.3A P-Channel V_{DS}=-15V, V_{GS}=-10V, I_D=-5.2A	N		2.2		nC
			P		10		
Gate-Source Charge	Q_{gs}		N		0.5		
			P		2.2		
Gate-Drain Charge	Q_{gd}		N		0.8		
			P		1.7		
Turn-On Delay Time	$t_{d(on)}$	N-Chaneel V_{DD}=15V, V_{GS}=10V, I_D=1A , R_{GEN}=6Ω, P-Channel V_{DD}=-15V, V_{GS}=-10V, I_D=-1A R_{GEN}=6Ω	N		8		nS
			P		10		
Rise Time	t_r		N		5		
			P		2.8		
Turn-Off Delay Time	$t_{d(off)}$		N		23		
			P		53.6		
Fall-Time	t_f		N		3		
			P		46		

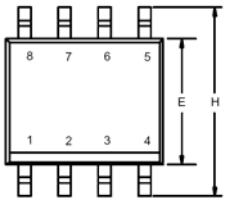
Notes

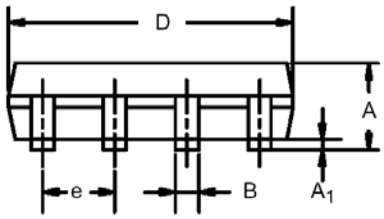
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Package Information

SO-8: 8LEAD





Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°